



P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 20	0.0155 at $V_{GS} = - 4.5$ V	- 13.4	36.5 nC
	0.0195 at $V_{GS} = - 2.5$ V	- 12	
	0.0250 at $V_{GS} = - 1.8$ V	- 10.5	

FEATURES

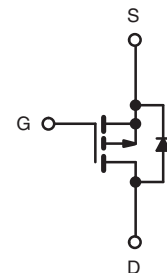
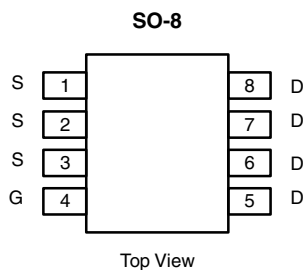
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Adaptor Switch
- High Current Load Switch
- Notebook



Ordering Information: Si4403CDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	$\pm$ 8	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	- 13.4	A
	$T_C = 70\text{ }^{\circ}\text{C}$		- 10.7	
	$T_A = 25\text{ }^{\circ}\text{C}$		- 9.4 ^{a, b}	
	$T_A = 70\text{ }^{\circ}\text{C}$		- 7.5 ^{a, b}	
Pulsed Drain Current		I_{DM}	- 40	
Continuous Source-Drain Diode Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_S	- 4.1	
	$T_A = 25\text{ }^{\circ}\text{C}$		- 2.1 ^{a, b}	
Avalanche Current	L = 0.1 mH	I_{AS}	- 15	
Single-Pulse Avalanche Energy		E_{AS}	11.25	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	5	W
	$T_C = 70\text{ }^{\circ}\text{C}$		3.2	
	$T_A = 25\text{ }^{\circ}\text{C}$		2.5 ^{a, b}	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.6 ^{a, b}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	38	50	°C/W
Maximum Junction-to-Foot	R_{thJF}	20	25	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. $t = 10$ s.

c. Maximum under steady state conditions is 85 °C/W.

d. Based on $T_C = 25$ °C.

Si4403CDY

Vishay Siliconix



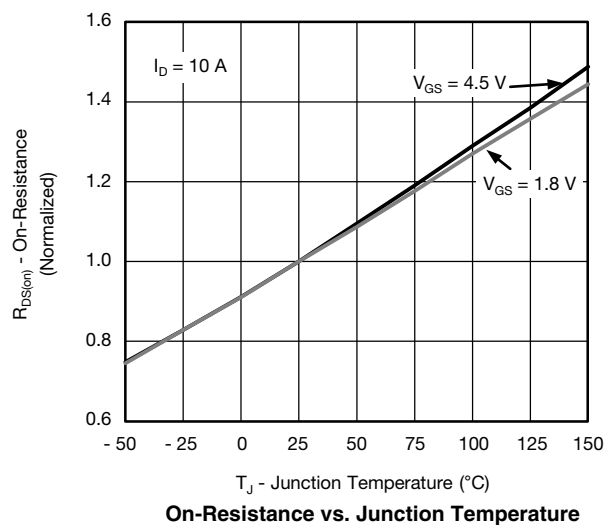
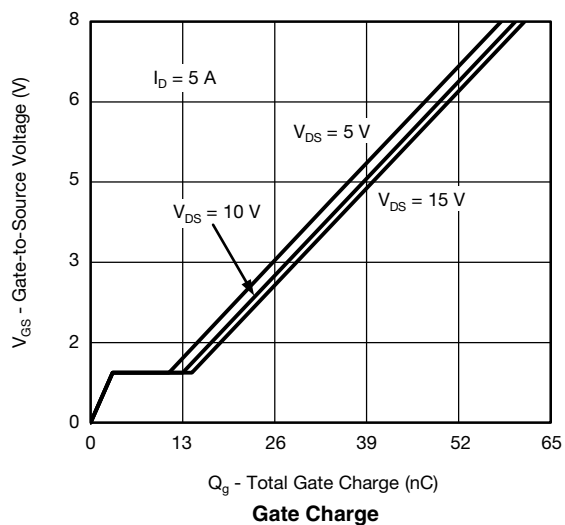
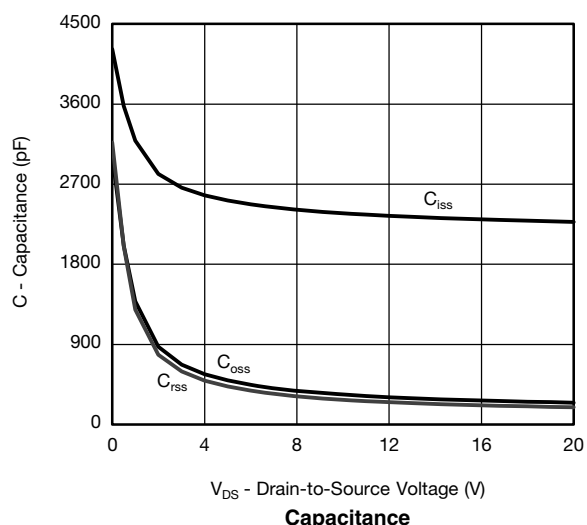
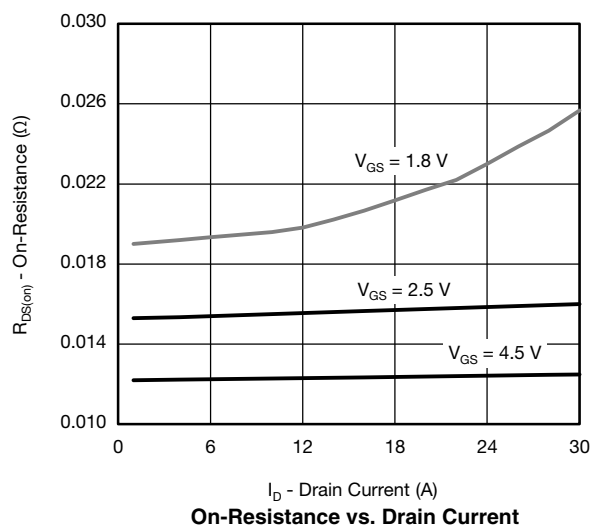
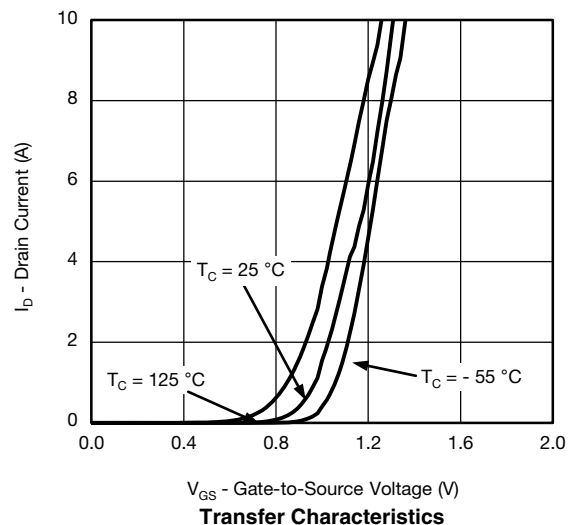
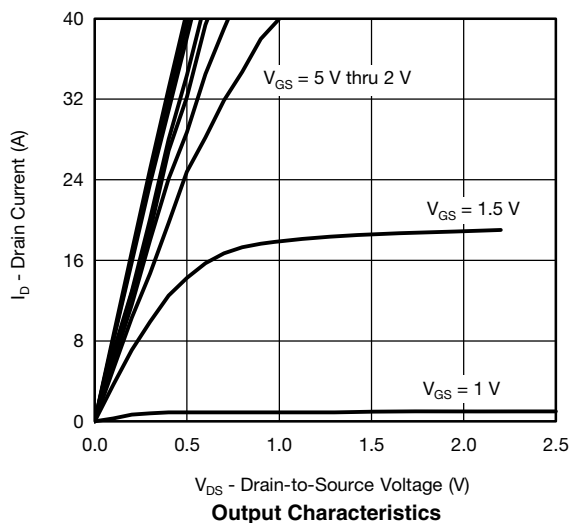
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 14.5		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.8		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 1.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 5 V	- 20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 9 A		0.0125	0.0155	Ω
		V _{GS} = - 2.5 V, I _D = - 6 A		0.0155	0.0195	
		V _{GS} = - 1.8 V, I _D = - 3 A		0.0195	0.0250	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 9 A		40		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		2380		pF
Output Capacitance	C _{oss}			340		
Reverse Transfer Capacitance	C _{rss}			280		
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 5 A		60	90	nC
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 5 A		36.5	55	
Gate-Drain Charge	Q _{gd}			3.1		
Gate Resistance	R _g			9.9		
Gate Resistance	R _g	f = 1 MHz	1.0	4.8	9.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2 Ω I _D ≅ - 5 A, V _{GEN} = - 8 V, R _g = 1 Ω		7	14	ns
Rise Time	t _r			9	18	
Turn-Off DelayTime	t _{d(off)}			108	200	
Fall Time	t _f			41	80	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2 Ω I _D ≅ - 5 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		14	28	
Rise Time	t _r			16	32	
Turn-Off DelayTime	t _{d(off)}			101	200	
Fall Time	t _f			40	80	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.1	A
Pulse Diode Forward Current	I _{SM}				- 40	
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.66	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 2.3 A, dl/dt = 100 A/μs, T _J = 25 °C		81	150	ns
Body Diode Reverse Recovery Charge	Q _{rr}			150	300	nC
Reverse Recovery Fall Time	t _a			43		ns
Reverse Recovery Rise Time	t _b			38		

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

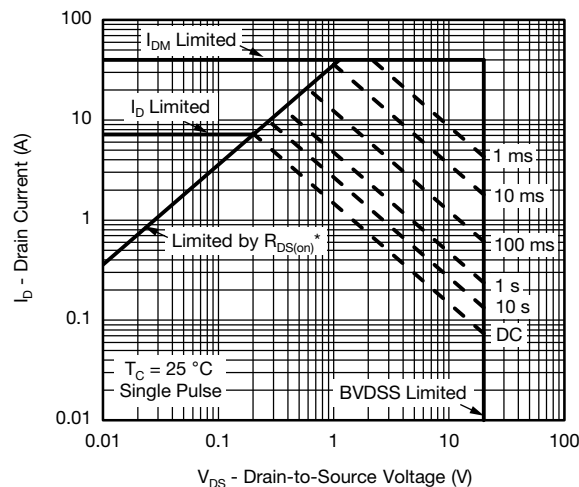
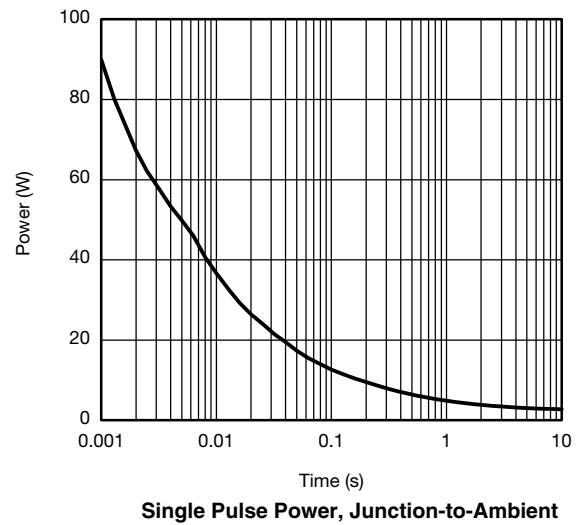
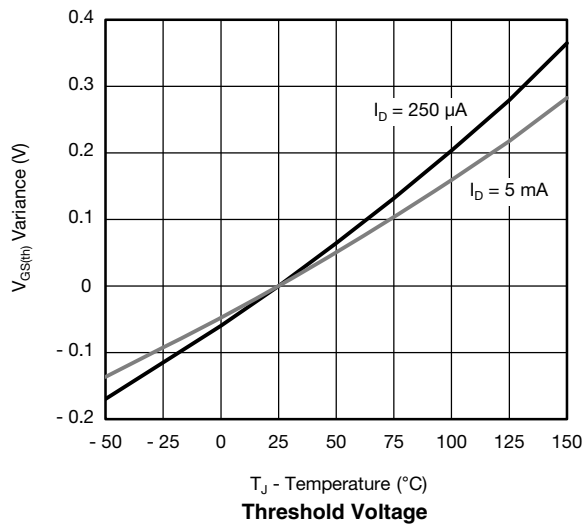
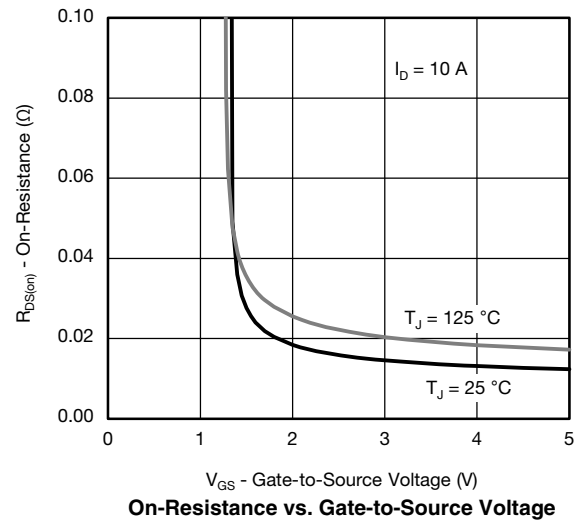
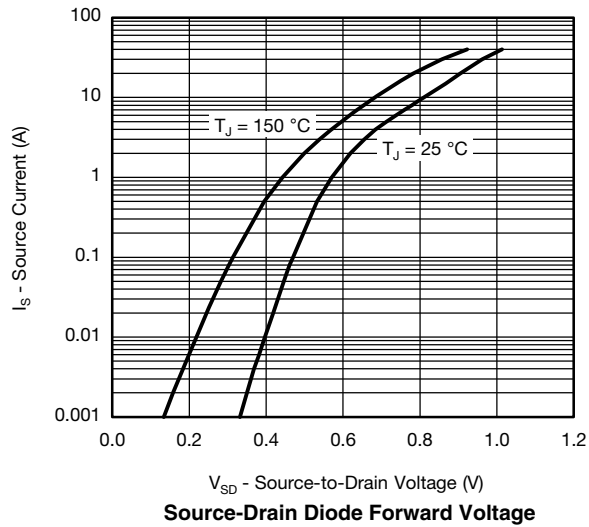
b. Guaranteed by design, not subject to production testing.

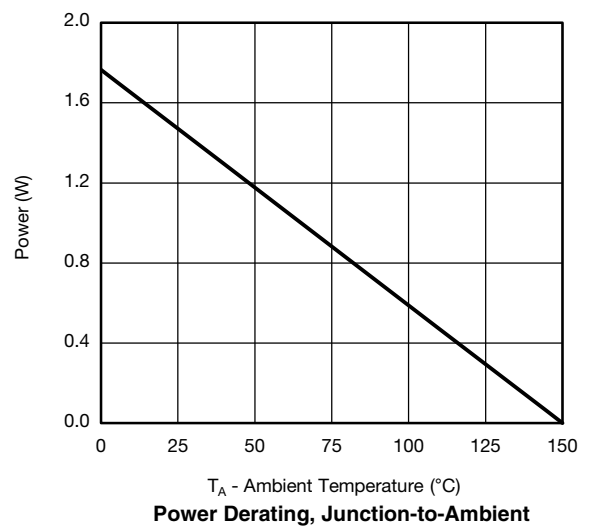
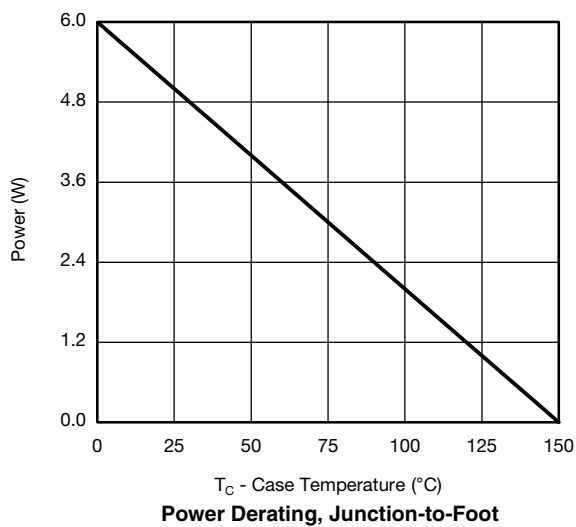
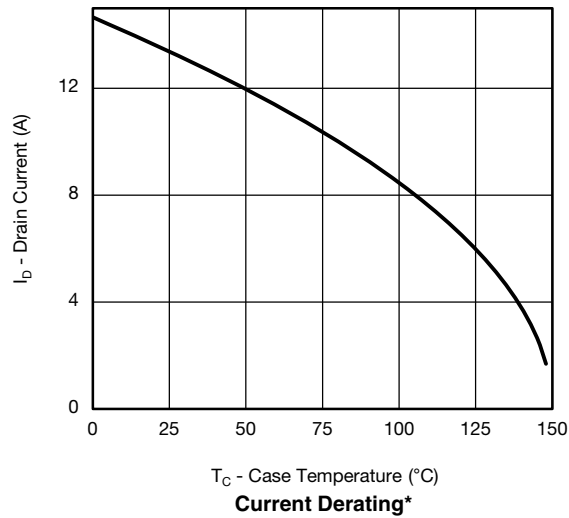
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

Si4403CDY

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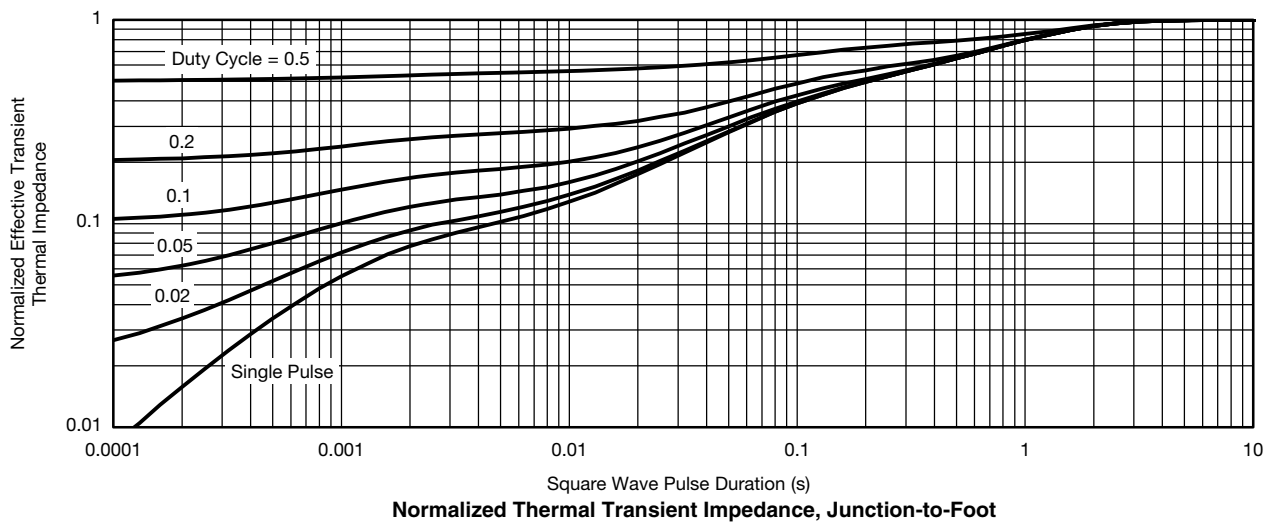
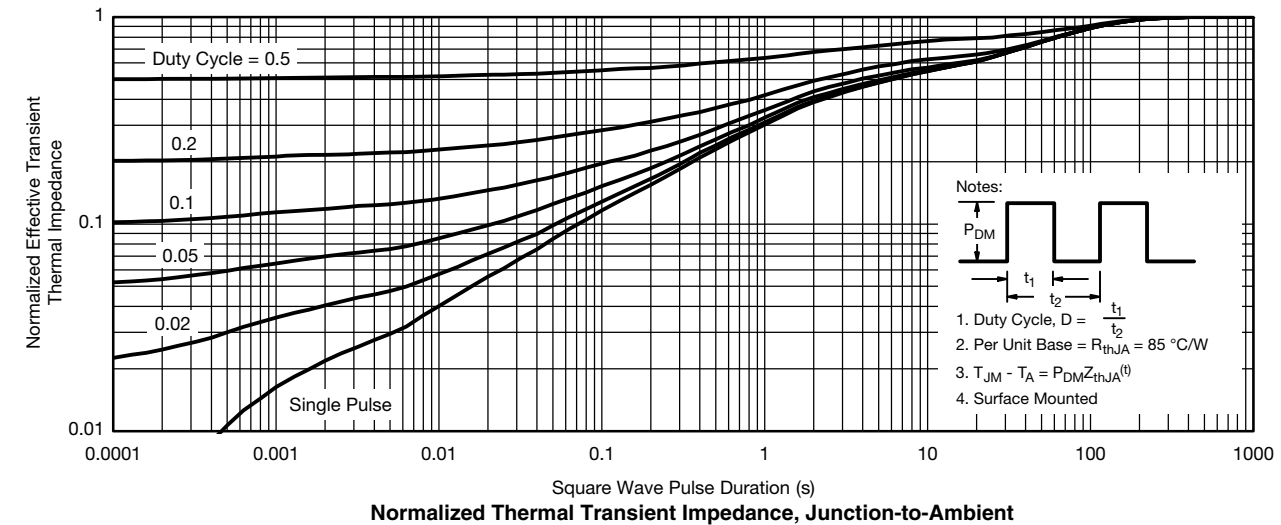
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67341.

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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